

CIRCUIT AND METHOD FOR REDUCING LEAKAGE CURRENT IN A ROW
DRIVER CIRCUIT IN A FLASH MEMORY DURING A STANDBY MODE OF
OPERATION

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ABSTRACT OF THE DISCLOSURE

A row driver receives an input signal and a test mode signal, and is coupled
10 to first and second voltage sources and has an output coupled to a word line. The row
driver operates in an active mode responsive to the test mode signal going inactive to
couple the output to either the first or second voltage source responsive to the input signal.
The row driver operates in a standby mode responsive to the test mode signal going active
to present a high impedance to the word line. A method includes detecting a first mode of
15 operation of a memory device and floating at least some of the word lines when the first
mode is detected. The memory device may be a flash memory device and the first mode
may be a standby mode of operation of the flash memory device.

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